



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	20V
I_D	3.0A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	50 mohm
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	70 mohm



YJL2302B

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Typical Performance Characteristics

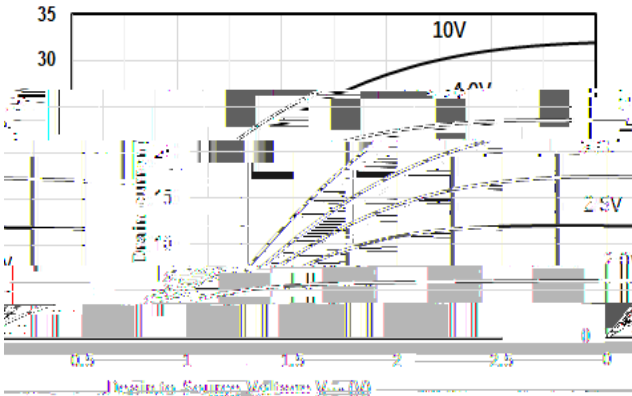


Figure1. Output Characteristics

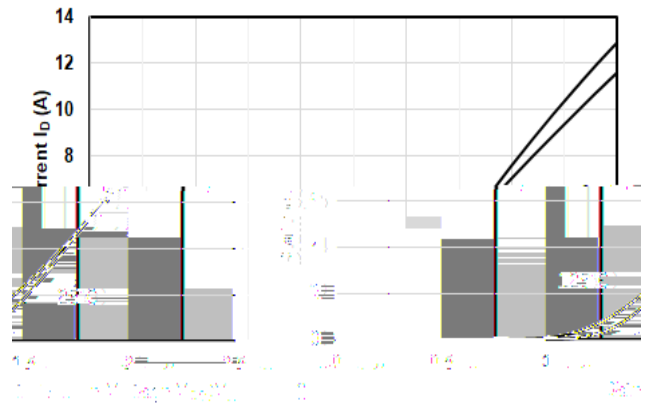


Figure2. Transfer Characteristics

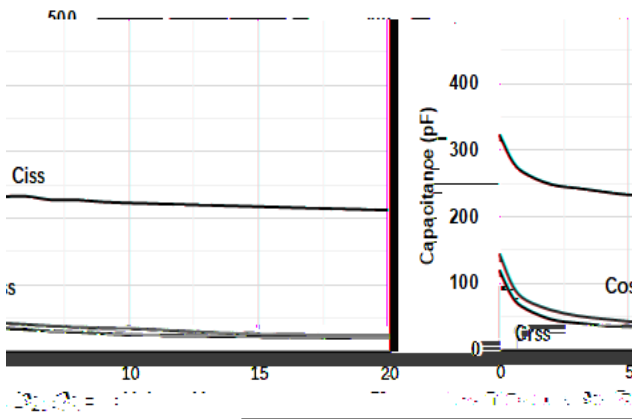


Figure3. Capacitance Characteristics

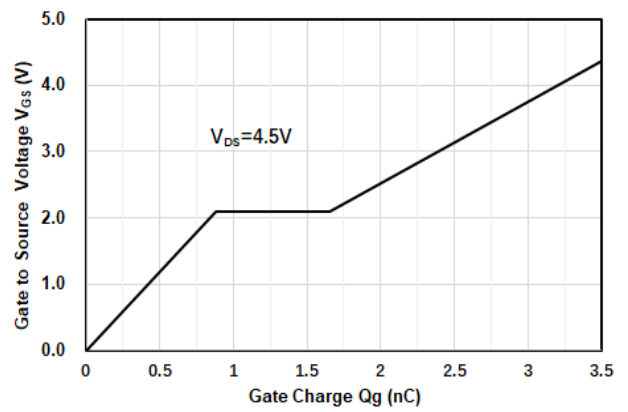


Figure4. Gate Charge

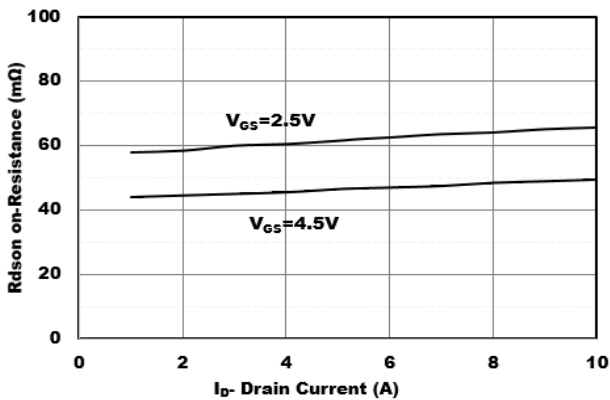


Figure5. Drain-Source on Resistance

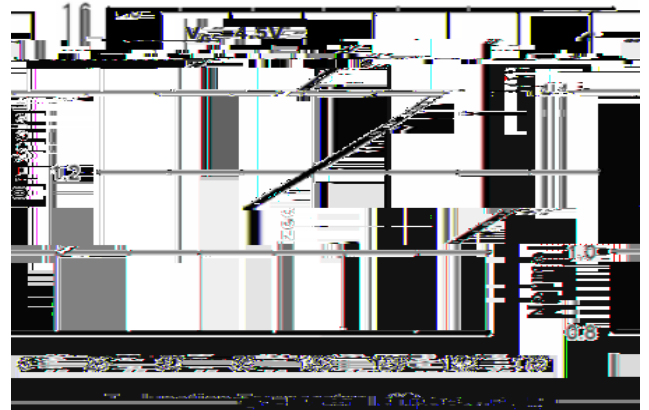


Figure6. Drain-Source on Resistance

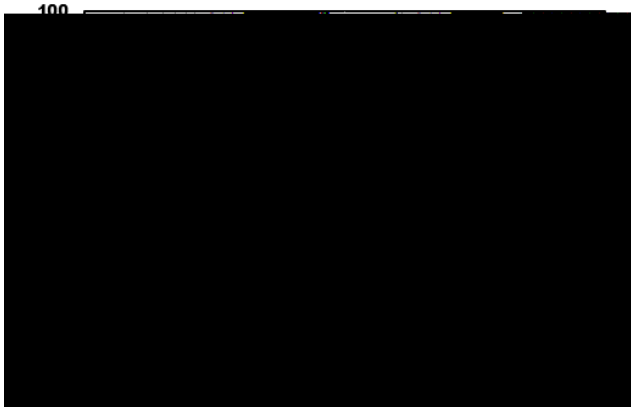


Figure 7. Safe Operation Area

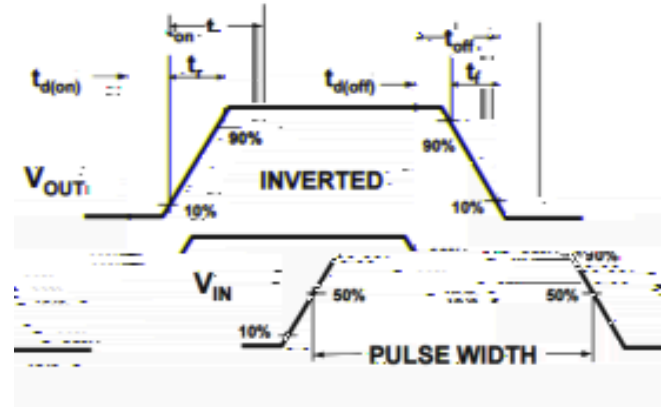


Figure 8. Switching wave

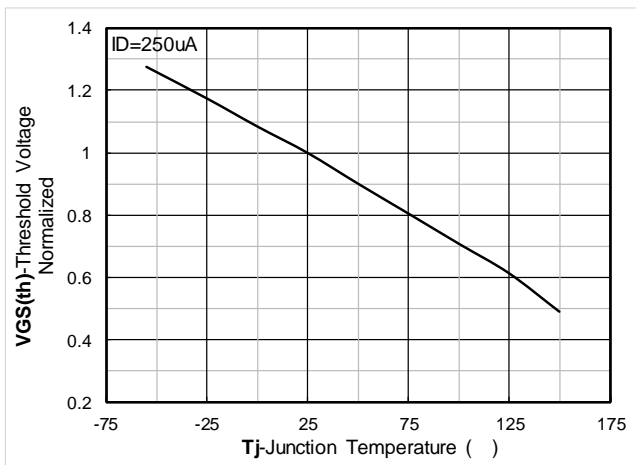


Figure 9. Normalized Threshold voltage

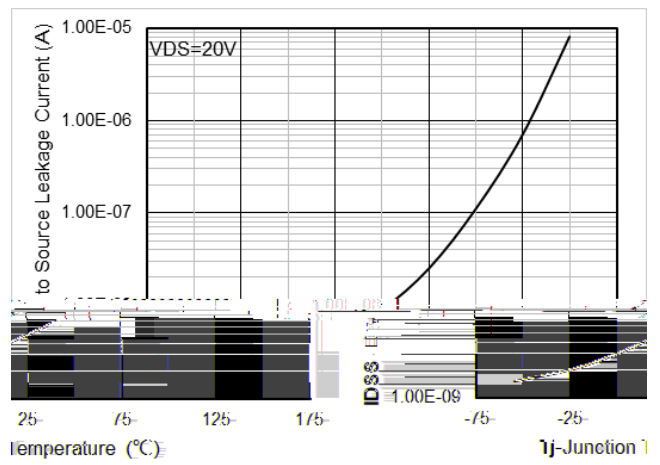
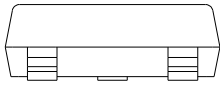
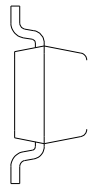
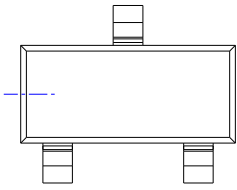


Figure 10. Drain to Source Leakage Current



SOT-23 Package information



UNIT mm

